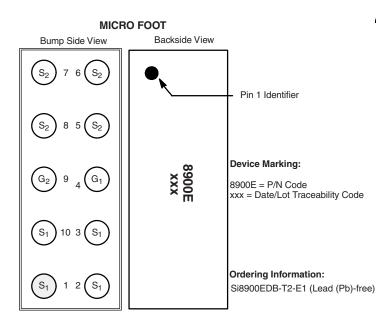


Vishay Siliconix

Bi-Directional N-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{S1S2} (V)	R _{S1S2(on)} (Ω)	I _{S1S2} (A)			
20	0.024 at V_{GS} = 4.5 V	7			
	0.026 at V _{GS} = 3.7 V	6.8			
	0.034 at V _{GS} = 2.5 V	5.0			
	0.040 at V _{GS} = 1.8 V	5.5			

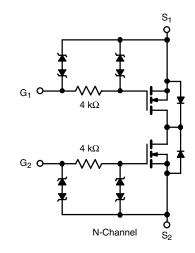


FEATURES

- TrenchFET[®] Power MOSFET
- Ultra-Low R_{SS(on)}
- ESD Protected: 4000 V
- MICRO FOOT[®] Chipscale Packaging Reduces Footprint Area Profile (0.62 mm) and On-Resistance Per Footprint Area

APPLICATIONS

Battery Protection Circuit
- 1-2 Cell Li+/LiP Battery Pack for Portable Devices



ABSOLUTE MAXIMUM RATINGS $T_A = 25 \degree C$, unless otherwise noted						
Parameter		Symbol	5 s	Steady State	Unit	
Source1- Source2 Voltage		V _{S1S2}	20		V	
Gate-Source Voltage		V _{GS}	± 12			
Continuous Source1- Source2 Current (T _J = 150 °C)	T _A = 25 °C		7	5.4		
	T _A = 85 °C	I _{S1S2}	5.1	3.9	А	
Pulsed Source1- Source2 Current		I _{SM}	50			
	T _A = 25 °C	P _D	1.8	1	W	
Maximum Power Dissipation ^a	T _A = 85 °C	- FD	0.9	0.5	vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	
Package Reflow Conditions ^c	IR/Convection		260			

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum lungtion to Ambienta	t ≤ 5 s	R _{thJA}	55	70		
Maximum Junction-to-Ambient ^a	Steady State		95	120	°C/W	
Maximum Junction-to-Foot ^b	Steady State	R _{thJF}	12	15		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. The foot is defined as the top surface of the package.

c. Refer to IPC/JEDEC (J-STD-020C), no manual or hand soldering.



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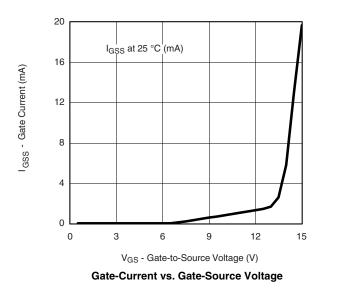
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static					1		
Gate Threshold Voltage	V _{GS(th)}	$V_{SS} = V_{GS}, I_{D} = 1.1 \text{ mA}$	0.45		1.0	V	
		$V_{SS} = 0 V, V_{GS} = \pm 4.5 V$			± 4	μA	
Gate-Body Leakage	I _{GSS}	$V_{SS} = 0 V, V_{GS} = \pm 12 V$			± 10	mA	
Zero Gate Voltage Drain Current	1	$V_{SS} = 20 V, V_{GS} = 0 V$			1		
	I _{S1S2}	V_{SS} = 20 V, V_{GS} = 0 V, T_{J} = 85 °C			5	μΑ	
On-State Drain Current ^a	I _{S(on)}	$V_{SS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	5			А	
		$V_{GS} = 4.5 \text{ V}, \text{ I}_{SS} = 1 \text{ A}$		0.020	0.024	Ω	
	a R _{S1S2(on)} –	$V_{GS} = 3.7 \text{ V}, \text{ I}_{SS} = 1 \text{ A}$		0.022	0.026		
Source1- Source2 On State Resistance ^a		$V_{GS} = 2.5 \text{ V}, \text{ I}_{SS} = 1 \text{ A}$		0.026	0.034		
		V _{GS} = 1.8 V, I _{SS} = 1 A		0.032	0.040		
Forward Transconductance ^a	9 _{fs}	V _{SS} = 10 V, I _{SS} = 1 A		31		S	
Dynamic ^b							
Turn-On Delay Time	t _{d(on)}			3	5		
Rise Time	t _r	V_{SS} = 10 V, R_L = 10 Ω		4.5	7		
Turn-Off Delay Time	t _{d(off)}	$I_{SS} \cong$ 1 A, V_{GEN} = 4.5 V, R_g = 6 Ω		55	85	μs	
Fall Time	t _f			15	25	1	

Notes:

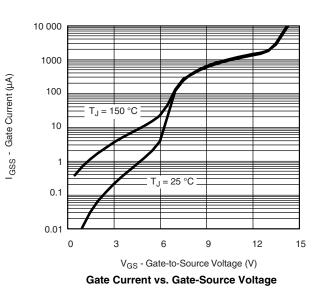
a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

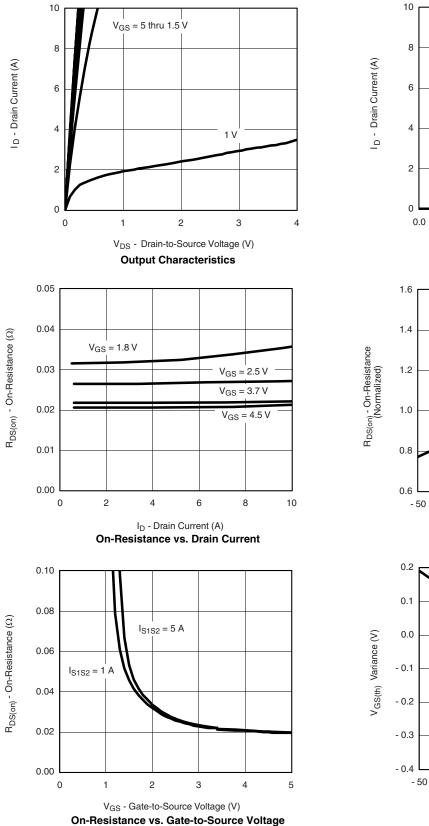


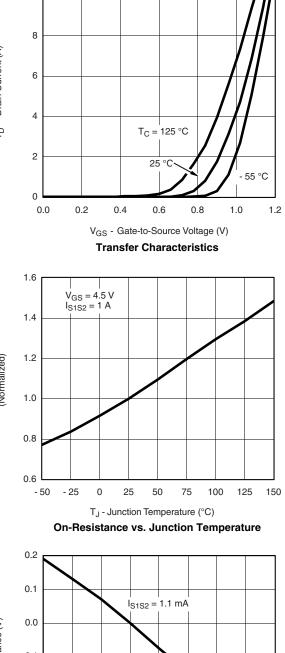


Si8900EDB

Vishay Siliconix

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





- 25

0

25

50

T_J - Temperature (°C)

Threshold Voltage

75

100

125

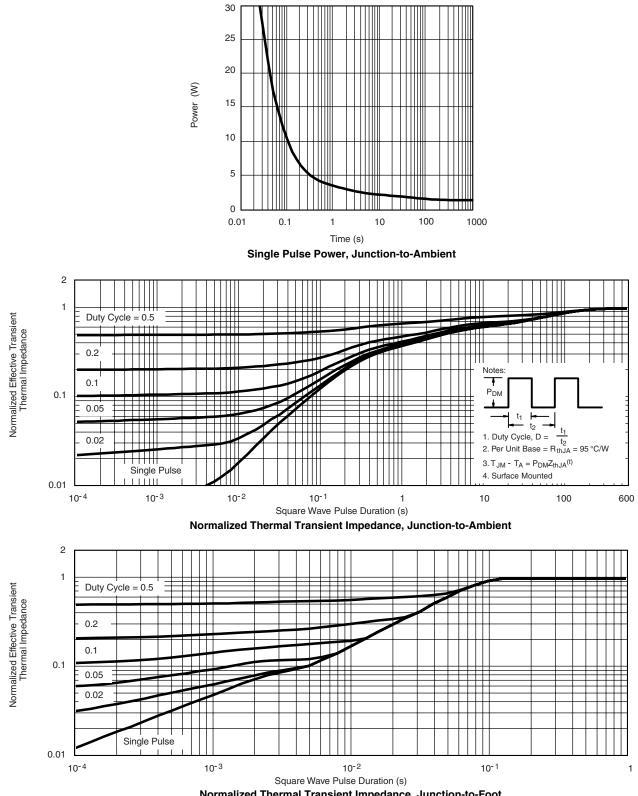
150

Si8900EDB

Vishay Siliconix



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

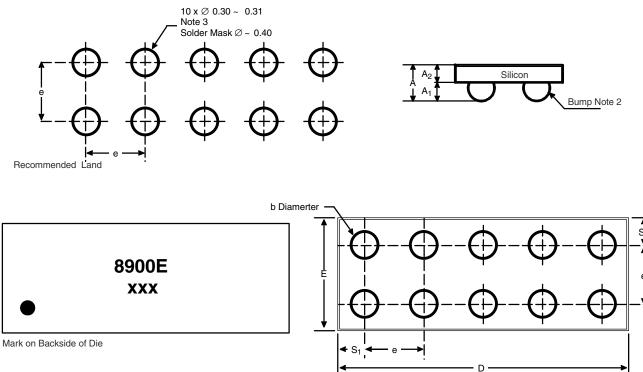




Si8900EDB Vishay Siliconix

PACKAGE OUTLINE

MICRO FOOT: 10-BUMP (2 x 5, 0.8 mm PITCH)



Notes (Unless Otherwise Specified):

1. Laser mark on the silicon die back, coated with a thin metal.

2. Bumps are 95.5Sn/3.8Ag/0.7Cu.

3. Non-solder mask defined copper landing pad.

Dim.	Millim	eters ^a	Inches		
	Min.	Max.	Min.	Max.	
Α	0.600	0.650	0.0236	0.0256	
A ₁	0.260	0.290	0.102	0.0114	
A ₂	0.340	0.360	0.0134	0.0142	
b	0.370	0.410	0.0146	0.0161	
D	4.050	4.060	0.1594	0.1598	
E	1.980	2.000	0.0780	0.0787	
e	0.750	0.850	0.0295	0.0335	
S ₁	0.430	0.450	0.0169	0.0177	
\$ ₂	0.580	0.600	0.0228	0.0236	

Notes:

a. Use millimeters as the primary measurement.

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